

STARPOWER

SEMICONDUCTOR™

IGBT

GD400SGL120C2S

Molding Type Module

1200V/400A 1 in one-package

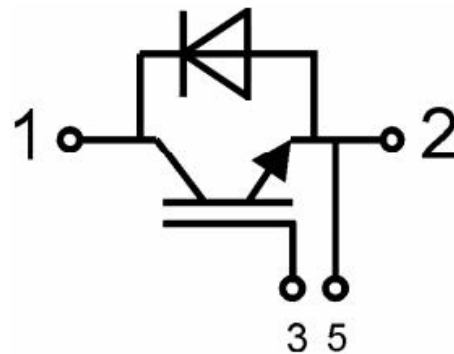
General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. It's designed for the applications such as Inverters and UPS.



Features

- High short circuit capability, self limiting to $6 \cdot I_C$
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Equivalent Circuit Schematic

Typical Applications

- AC inverter drives
- Switching mode power supplies
- Electronic welders at f_{sw} up to 20kHz

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Description	GD400SGL120C2S	Units
V_{CES}	Collector-Emitter Voltage	1200	V

Symbol	Description	GD400SGL120C2S	Units
V_{GES}	Gate-Emitter Voltage	$\pm 20V$	V
I_C	Collector Current @ $T_C=25^{\circ}C$, $T_J=150^{\circ}C$ @ $T_C=80^{\circ}C$, $T_J=150^{\circ}C$	650	A
		400	
$I_{CM(1)}$	Pulsed Collector Current @ $T_C=80^{\circ}C$	800	A
I_F	Diode Continuous Forward Current	400	A
I_{FM}	Diode Maximum Forward Current	800	A
P_D	Maximum power Dissipation @ $T_J=150^{\circ}C$	2500	W
T_{SC}	Short Circuit Withstand Time @ $T_J=125^{\circ}C$	10	μs
T_J	Operating Junction Temperature	-40 to +150	$^{\circ}C$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}C$
I^2t -value, Diode	$V_R=0V$, $t=10ms$, $T_J=125^{\circ}C$	27500	A^2s
V_{ISO}	Isolation Voltage RMS, $f=50Hz$, $t=1min$	2500	V
Mounting Torque	Power Terminal Screw:M6	2.5 to 5	N.m
	Mounting Screw:M6	3 to 6	N.m

Notes:

(1) Repetitive rating: Pulse width limited by max. junction temperature

Electrical Characteristics of IGBT $T_C=25^{\circ}C$ unless otherwise noted**Off Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{CES}	Collector-Emitter Breakdown Voltage	$T_J=25^{\circ}C$	1200			V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}$, $V_{GE}=0V$, $T_J=25^{\circ}C$			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}$, $V_{CE}=0V$, $T_J=25^{\circ}C$			400	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=8mA$, $V_{CE}=V_{GE}$, $T_J=25^{\circ}C$	5.0	6.2	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=400A$, $V_{GE}=15V$, $T_J=25^{\circ}C$		1.9		V
		$I_C=400A$, $V_{GE}=15V$, $T_J=125^{\circ}C$		2.1		

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V$, $I_C=400A$, $R_G=4\Omega$, $V_{GE}=\pm 15V$, $T_J=25^{\circ}C$		100		ns
t_r	Rise Time			60		ns
$t_{d(off)}$	Turn-Off Delay Time			420		ns

t_f	Fall Time	$V_{CC}=600V, I_C=400A,$ $R_G=4\Omega, V_{GE} = \pm 15V,$ $T_J=25^\circ C$		60		ns
E_{on}	Turn-On Switching Loss			33		mJ
E_{off}	Turn-Off Switching Loss			42		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600V, I_C=400A,$ $R_G=4\Omega, V_{GE} = \pm 15V,$ $T_J=125^\circ C$		120		ns
t_r	Rise Time			60		ns
$t_{d(off)}$	Turn-Off Delay Time			490		ns
t_f	Fall Time			75		ns
E_{on}	Turn-On Switching Loss			35		mJ
E_{off}	Turn-Off Switching Loss			46		mJ
C_{ies}	Input Capacitance	$V_{CE} = 25V, f=1MHz,$ $V_{GE} = 0V$		30		nF
C_{oes}	Output Capacitance			4		nF
C_{res}	Reverse Transfer Capacitance			3		nF
I_{SC}	SC Data	$t_{SC} \leq 10\mu s, V_{GE}=15V,$ $T_J=125^\circ C, V_{CC}=900V,$ $V_{CEM} \leq 1200V$		1900		A
L_{CE}	Stray inductance				20	nH
$R_{CC'+EE'}$	Module lead resistance, terminal to chip	$T_C=25^\circ C$		0.18		m Ω

Electrical Characteristics of DIODE $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V _F	Diode Forward Voltage	I _F =400A	T _J =25°C		2.1	2.2	V
			T _J =125°C		2.2	2.3	
Q _r	Diode Reverse Recovery Charge	I _F =400A, V _R =600V, di/dt=-4000A/μs, V _{GE} =-15V	T _J =25°C		40		μC
			T _J =125°C		48		
I _{RM}	Diode Peak Reverse Recovery Current		T _J =25°C		320		A
			T _J =125°C		400		
E _{rec}	Reverse Recovery Energy		T _J =25°C		12		mJ
			T _J =125°C		20		

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (IGBT Part, per Module)		0.05	K/W
$R_{\theta JC}$	Junction-to-Case (DIODE Part, per Module)		0.09	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.035		K/W
Weight	Weight of Module	310		g

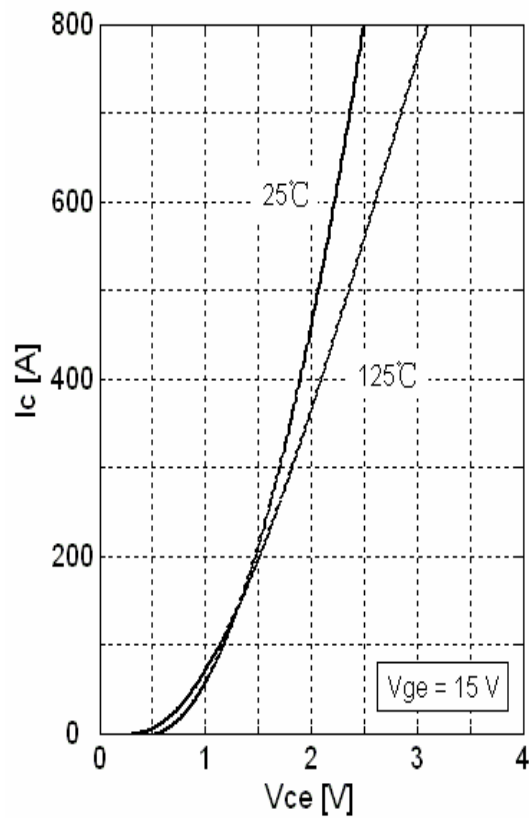


Fig 1. Typical Output Characteristics

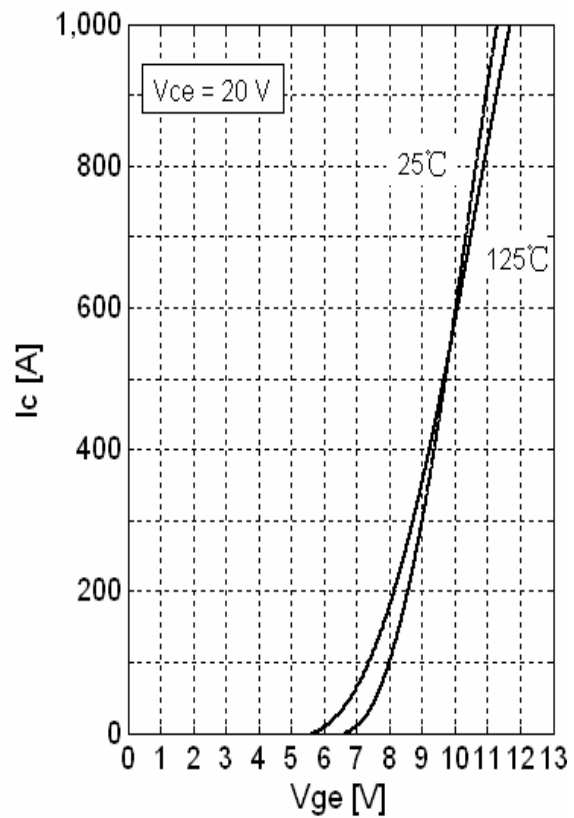


Fig 2. Typical Transfer Characteristics

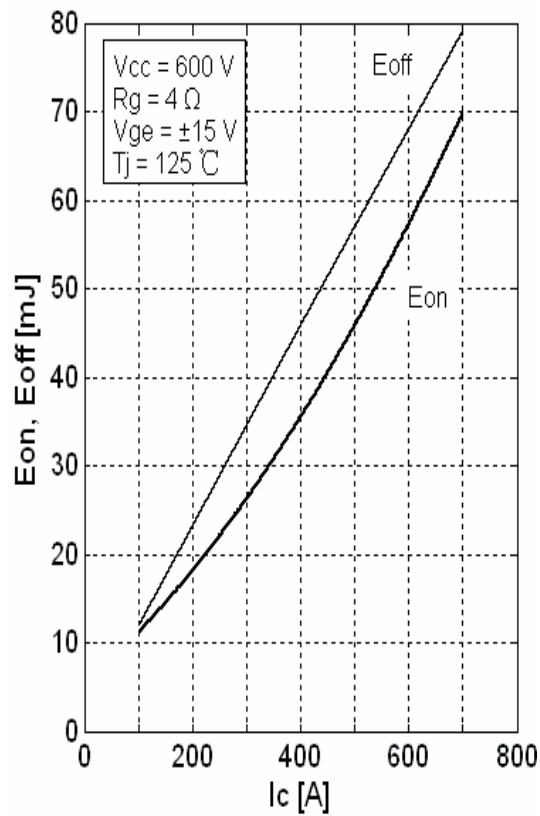


Fig 3. Switching Loss vs Collector Current

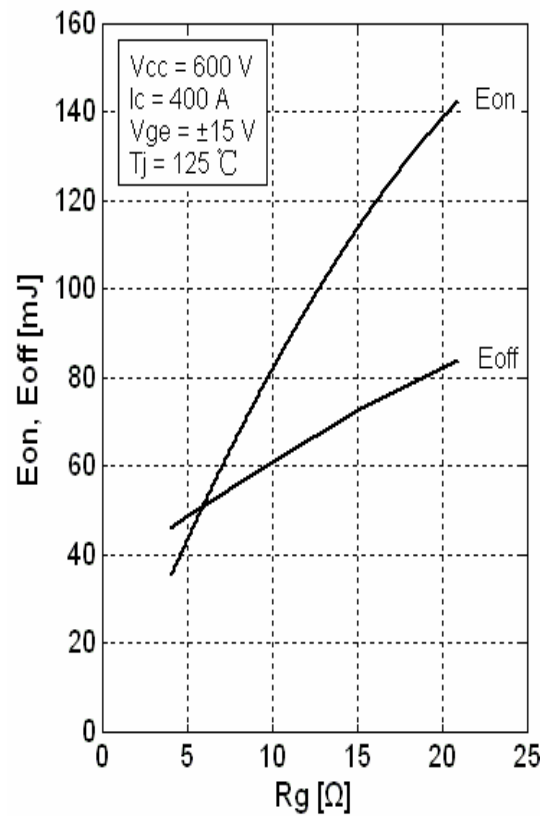


Fig 4. Switching Loss vs Gate Resistor

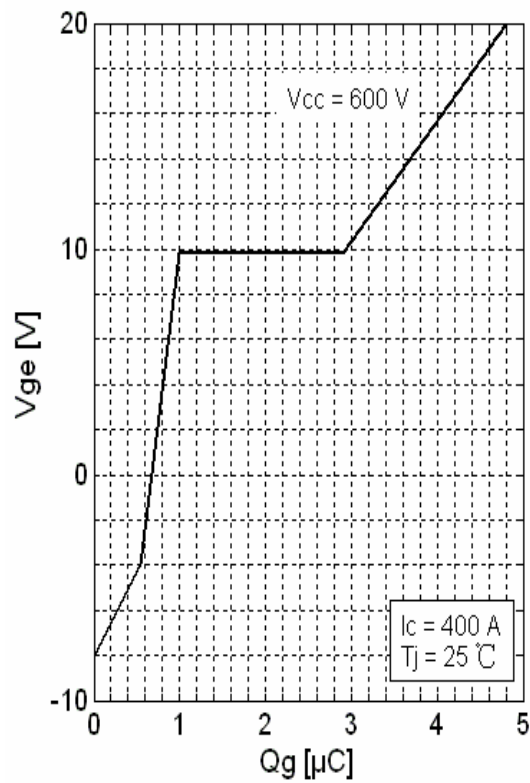
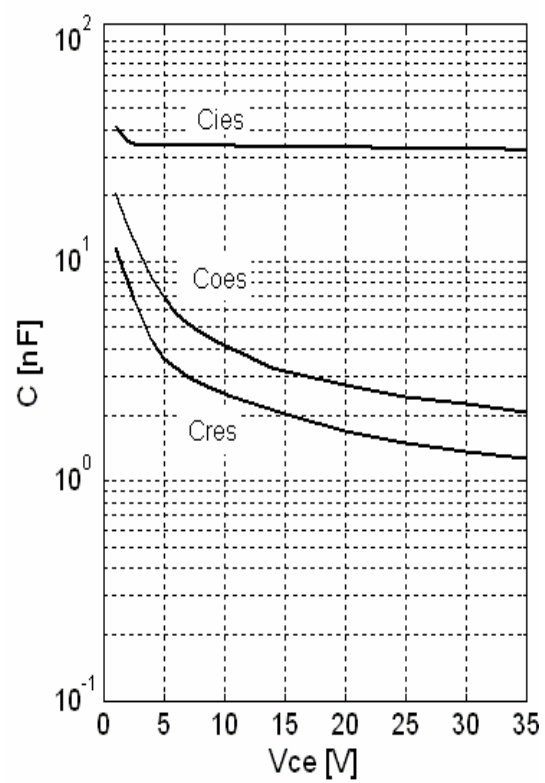
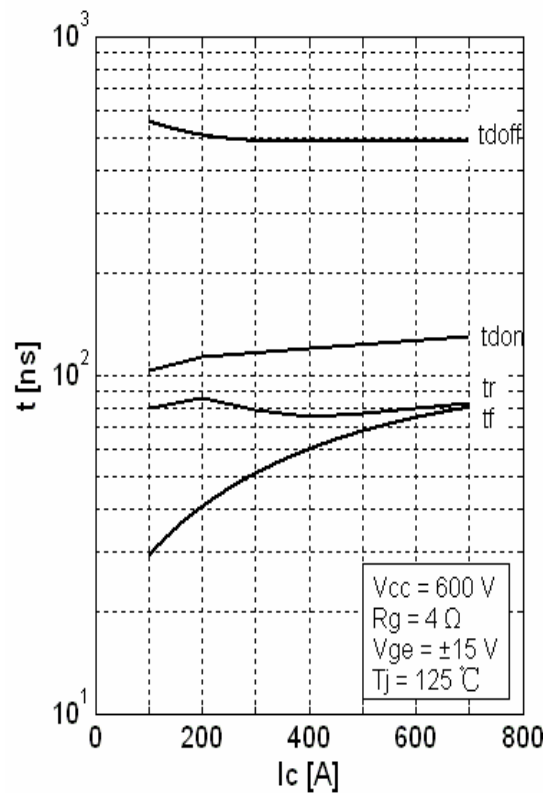
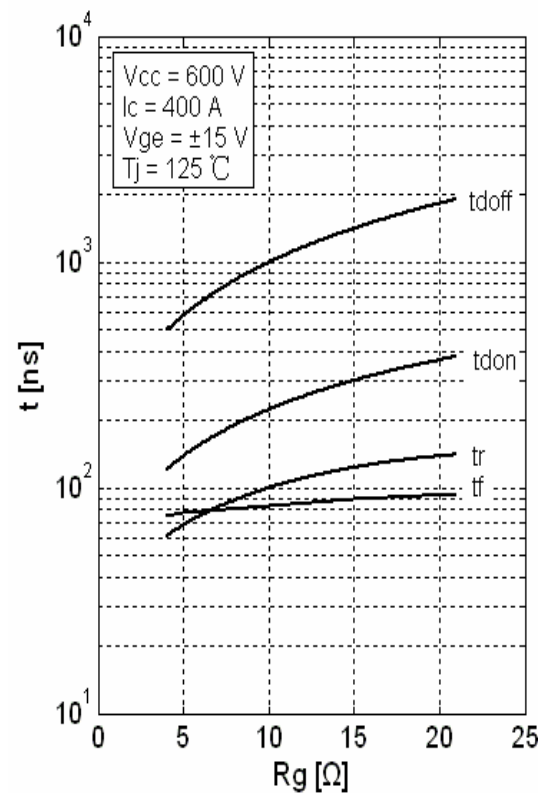


Fig 5. Gate Charge Characteristics.

Fig 6. Typical Capacitance vs
Collector-Emitter VoltageFig 7. Typical Switching Times vs I_c Fig 8. Typical Switching Times vs Gate
Resistance R_g

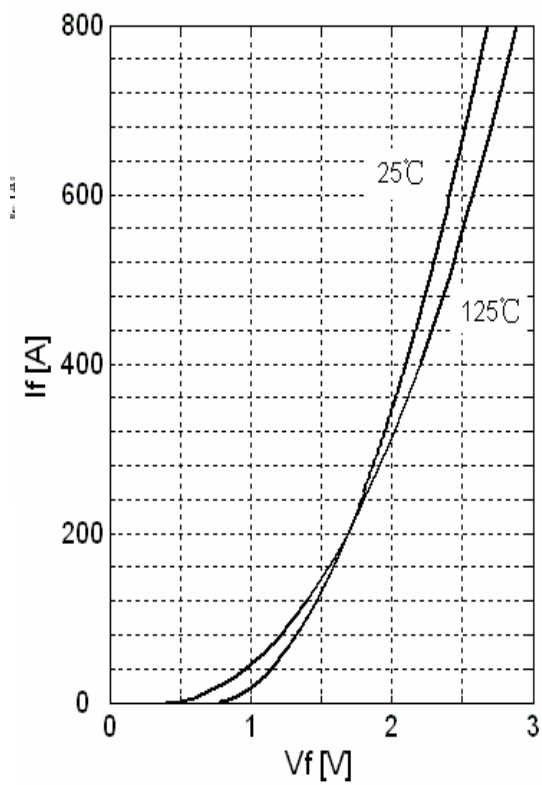


Fig 9. Typical Forward Characteristics (diode)

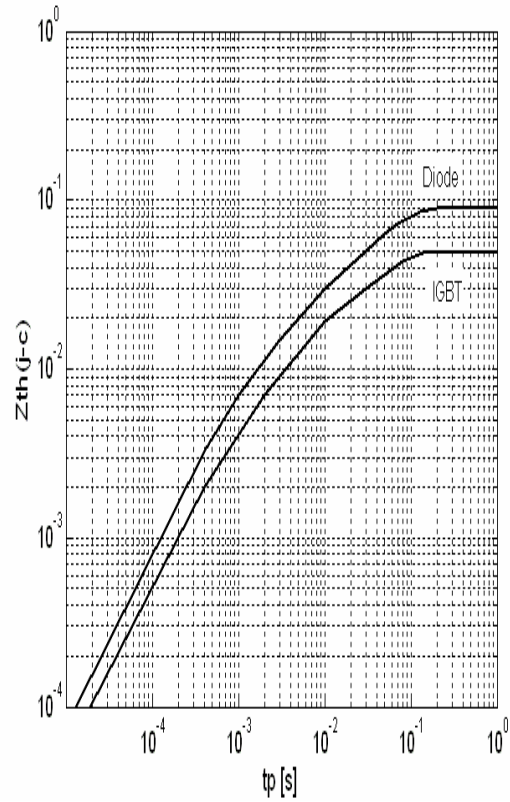


Fig 10. Transient thermal impedance

Package Dimension

Dimensions in Millimeters

